2022년 1월 26일(수), 10:45-12:30 Room B (에메랄드 II+III, 5층)

D. Thin Film Process Technology 분과 [WB2-D] Ferroelectrics

좌장: 박민혁 교수(서울대학교), 안지훈 교수(한양대학교) W 전극 위에 증착된 플루오라이트 구조 Hfa₅Zra₅O₂ 강유전성 박막의 우수한 강 유전성에 관한 연구 Kun Yang¹, Ju Yong Park¹, Dong Hyun Lee¹, Jin Joo Ryu^{3,4}, Gun Hwan Kim³, and Min WB2-D-1 Hvuk Park² 10:45-11:00 ¹School of Materials Science and Engineering, Pusan National University, ²Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University, 3 Center for Thin Film Materials, KRICT, 4 Department of Materials Science and Engineering, Yonsei University Operando Transmission Electron Microscopy Investigation on Domain **Dynamics in Two Dimensional Ferroelectric Materials** WB2-D-2 11:00-11:30 Hyobin Yoo Sogang University Theoretical Understanding of the Phase Formation in (Hf_{1.x}Zr_x)O₂; Effects of Composition, Thermodynamics and Kinetics Kun Hee Ye^{1,2}, Taeyoung Jeoung^{1,2}, Seungjae Yoon^{1,2}, Cheol Seong Hwang², and WB2-D-3 Jung-Hae Choi1 11:30-11:45 ¹Electronic Materials Research Center, KIST, ²Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University Effects of Deposition and Annealing Temperatures on the Characteristics of WB2-D-4 Hf_{0.5}Zr_{0.5}O₂ Thin Film Prepared by Plasma Enhanced Atomic Layer Deposition Hak Gyeong Kim, Da Hee Hong, Jae Hoon Yu, and Hee Chul Lee 11:45-12:00 Department of Advanced Materials Engineering, Korea Polytechnic University Self-Rectifying Ferroelectric Tunnel Junction by Imprint Field Engineering WB2-D-5 Youngin Goh, Junghyeon Hwang, Minki Kim, Minhyun Jung, and Sanghun Jeon 12:00-12:15 Korea School of Electrical Engineering, KAIST Ti 박막층의 Direct Scavenging Effect를 이용한 Mo/Hf0.3Zr0.7O2/Si Capacitor의 반강유전성 및 Endurance 특성의 개선에 대한 연구 Se Hyun Kim¹, Geun Taek Yu¹, Geun Hyeong Park¹, Dong Hyun Lee¹, Ju Yong Park¹, WB2-D-6

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Kun Yang¹, and Min Hyuk Park²

Center, Seoul National University

12:15-12:30